NPN Darlington Transistors

FEATURES

- High Current Gain

MAXIMUM RATINGS(Ta=25 unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	80	V
Collector-base voltage	V_{CBO}	80	
Emitter-base voltage	V_{EBO}	12	
Collector current	I_C	500	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	°C/W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 +150	

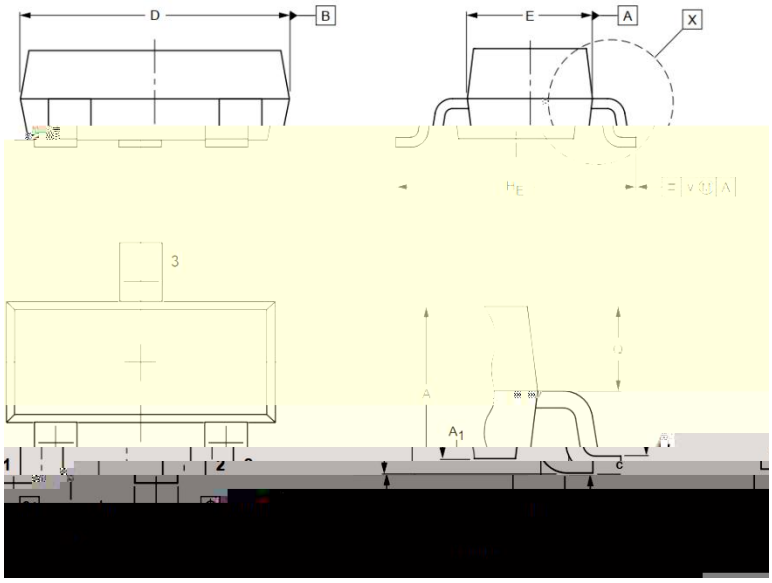
Typical Characteristics

Ordering information

Package	Packing Description	Base Quantity	Packing Quantity
SOT-23			

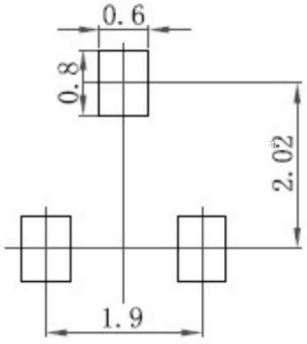
Package Dimensions

SOT-23



Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

The recommended mounting pad size



The information presented in this document is for reference only. GuangDong